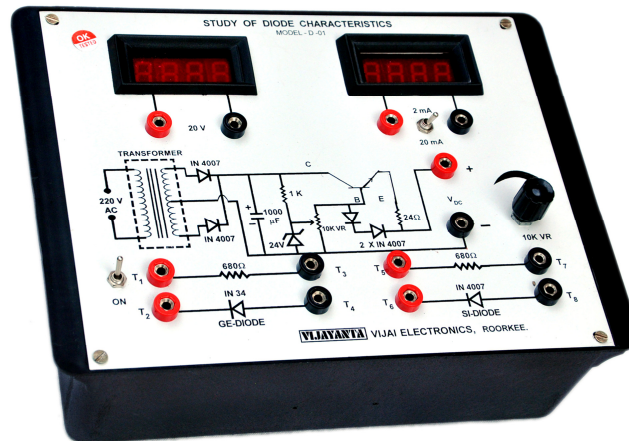


## CHARACTERISTICS OF P.N. JUNCTION DIODE (Ge & Si) AND COMPARAISON, MODEL : D - 01.



### FEATURES :

- \*\* Builtin Regulated, continuously variable and short circuit proof power supply suitable for the experimental board.
- \*\* Circuit is engraved and components are mounted on the top of the painted aluminum sheet to give better and clear understanding.
- \*\* A complete working manual containing theory, circuit details and operating instruction supplied with the experimental board.
- \*\* Stackable type connecting leads suitable to the terminals are supplied with the board for easy inter - connections and longer life of the terminals.
- \*\* Weight : 2.5 Kg Approximately
- \*\* Dimension : 210mm × 280mm × 82mm

### EXPERIMENTS :

1. Forward and Reverse Characteristics of Germanium Diode.
2. Forward Characteristics of Silicon Diode.

### OTHER APPARATUS REQUIRED :

- |                          |                        |         |
|--------------------------|------------------------|---------|
| 1. Digital Voltmeter.    | Range : 0 - 20, Volts. | One No. |
| 2. Digital Milliammeter. | Range : 0 - 20, mAmps. | One No. |
| 3. Digital Milliammeter. | Range : 0 - 2, mAmps.  | One No. |

*NOTE: There may be any change in specification due to continuous R & D without notice.*

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